

RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

Designed for Class A and Class AB PCN and PCS base station applications with frequencies up to 2600 MHz. Suitable for FM, TDMA, CDMA, and multicarrier amplifier applications.

- Specified Two-Tone Performance @ 2000 MHz, 26 Volts
 - Output Power — 10 Watts PEP
 - Power Gain — 10.5 dB
 - Efficiency — 28%
 - Intermodulation Distortion — -31 dBc
- Specified Single-Tone Performance @ 2000 MHz, 26 Volts
 - Output Power — 10 Watts CW
 - Power Gain — 9.5 dB
 - Efficiency — 35%
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 2000 MHz, 10 Watts CW Output Power

Features

- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- RoHS Compliant
- Available in Tape and Reel. R1 Suffix = 500 Units per 12 mm, 7 inch Reel.

MRF282SR1

**2000 MHz, 10 W, 26 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFET**



**CASE 458B-03, STYLE 1
NI-200S**

ARCHIVE INFORMATION

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Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	60 0.34	W $\text{W}/^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Case Operating Temperature	T_C	150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.2	$^\circ\text{C}/\text{W}$

Table 3. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

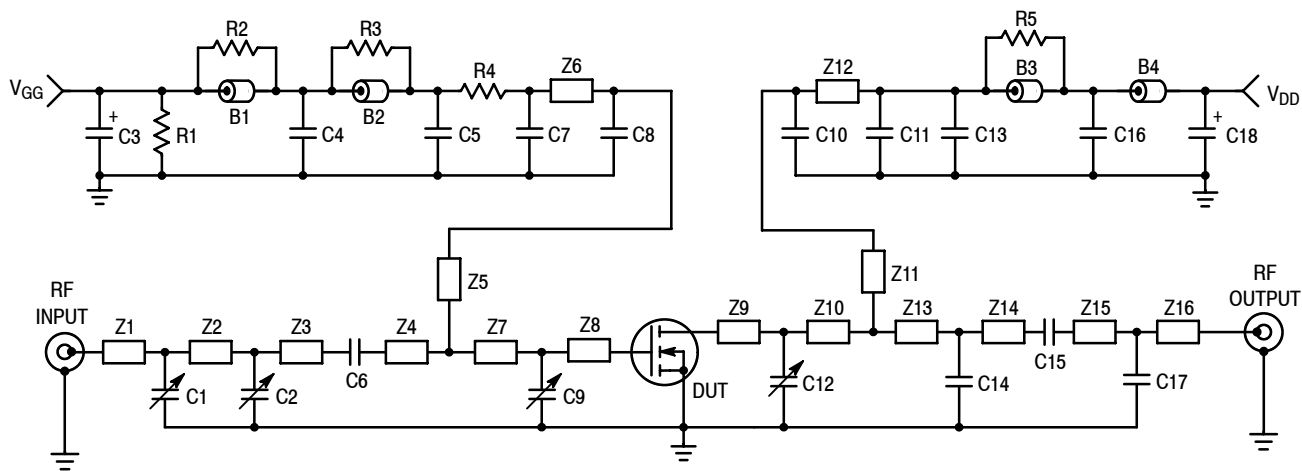
Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 10 \mu\text{Adc}$)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 28 \text{ Vdc}$, $V_{GS} = 0$)	I_{DSS}	—	—	1.0	μAdc
Gate-Source Leakage Current ($V_{GS} = 20 \text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	—	—	1.0	μAdc

Off Characteristics

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

Table 3. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 50\ \mu\text{Adc}$)	$V_{GS(th)}$	2.0	3.0	4.0	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 0.5\text{ Adc}$)	$V_{DS(on)}$	—	0.4	0.6	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 75\text{ mAdc}$)	$V_{GS(q)}$	3.0	4.0	5.0	Vdc
Dynamic Characteristics					
Input Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{iss}	—	15	—	pF
Output Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{oss}	—	8.0	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{rss}	—	0.45	—	pF
Functional Tests (In Freescale Test Fixture)					
Common-Source Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 10\text{ W PEP}$, $I_{DQ} = 75\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	G_{ps}	10.5	11.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 10\text{ W PEP}$, $I_{DQ} = 75\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	η	28	—	—	%
Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 10\text{ W PEP}$, $I_{DQ} = 75\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	IMD	—	-31	-28	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 10\text{ W PEP}$, $I_{DQ} = 75\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	IRL	—	-14	-9	dB
Common-Source Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 10\text{ W CW}$, $I_{DQ} = 75\text{ mA}$, $f = 2000.0\text{ MHz}$)	G_{ps}	9.5	11.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 10\text{ W CW}$, $I_{DQ} = 75\text{ mA}$, $f = 2000.0\text{ MHz}$)	η	35	40	—	%

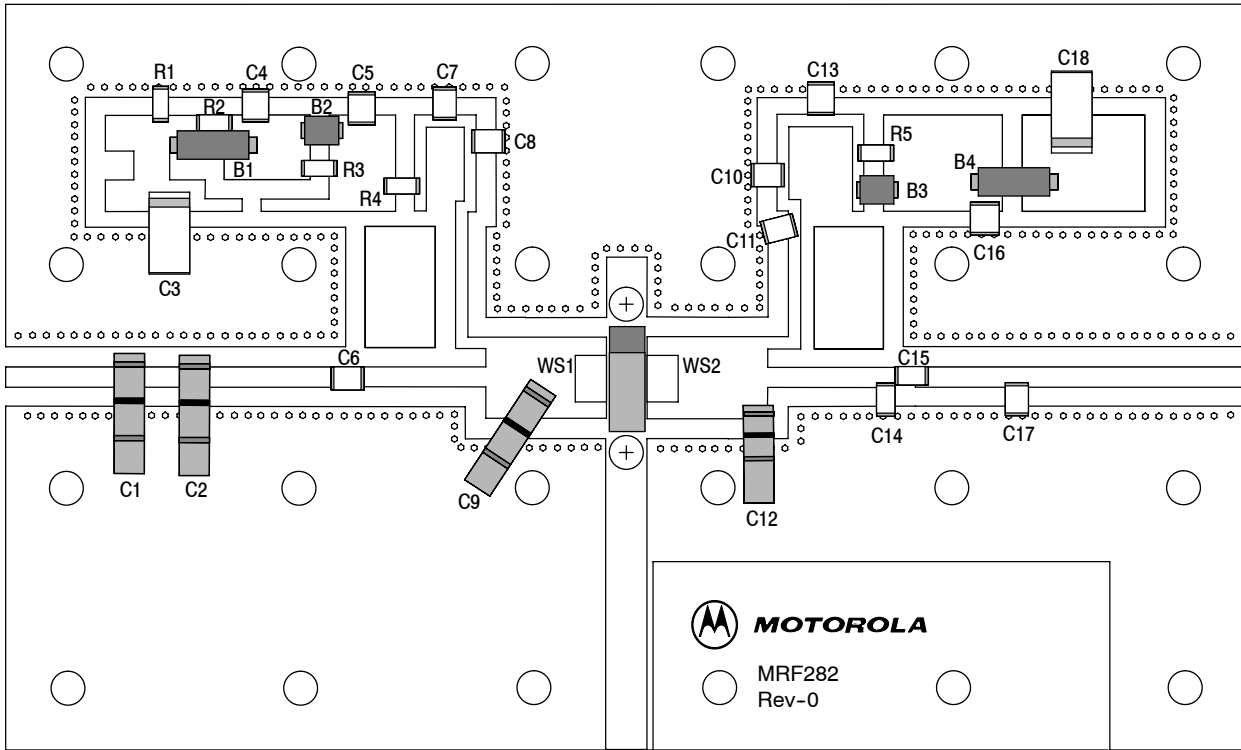


Z1	0.491" x 0.080" Microstrip	Z11	0.636" x 0.055" Microstrip
Z2	0.253" x 0.080" Microstrip	Z12	0.303" x 0.055" Microstrip
Z3	0.632" x 0.080" Microstrip	Z13	0.463" x 0.080" Microstrip
Z4	0.567" x 0.080" Microstrip	Z14	0.105" x 0.080" Microstrip
Z5	1.139" x 0.055" Microstrip	Z15	0.452" ± 0.085" x 0.080" Microstrip
Z6	0.236" x 0.055" Microstrip	Z16	0.910" ± 0.085" x 0.080" Microstrip
Z7	0.180" x 0.325" Microstrip	PCB	0.030" Glass Teflon®, 2 oz Copper, 3" x 5" Dimensions, Arlon GX0300-55-22, $\epsilon_r = 2.55$
Z8	0.301" x 0.325" Microstrip		
Z9	0.439" x 0.325" Microstrip		
Z10	0.055" x 0.325" Microstrip		

Figure 1. 1930 - 2000 MHz Broadband Test Circuit Schematic

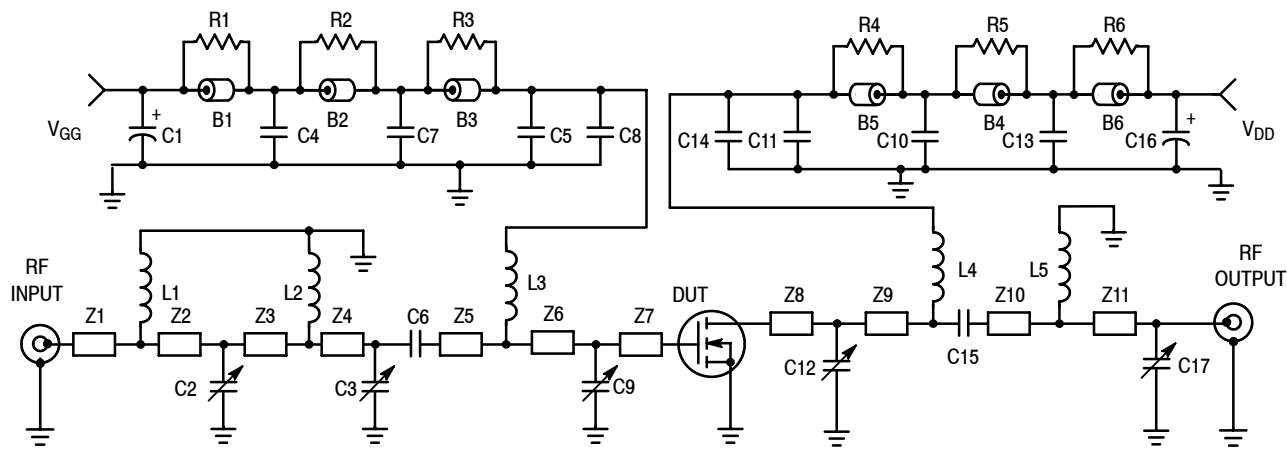
Table 4. 1930 - 2000 MHz Broadband Test Circuit Component Designations and Values

Designators	Description
B1, B4	Surface Mount Ferrite Beads, 0.120" x 0.333" x 0.100", Fair Rite #2743019446
B2, B3	Surface Mount Ferrite Beads, 0.120" x 0.170" x 0.100", Fair Rite #2743029446
C1, C2, C9	0.8–8.0 pF Variable Capacitors, Johanson Gigatrim #27291SL
C3	10 μ F, 35 V Tantalum Surface Mount Chip Capacitor, Kemet #T495X106K035AT
C4, C5, C13, C16	0.1 μ F Chip Capacitors, Kemet #CDR33BX104AKYS
C6	200 pF Chip Capacitor, ATC #100B201JT500XT
C7	18 pF Chip Capacitor, ATC #100B180KT500XT
C8	39 pF Chip Capacitor, ATC #100B390JT500XT
C10	27 pF Chip Capacitor, ATC #100B270JT500XT
C11	1.2 pF Chip Capacitor, ATC #100B1R2CT500XT
C12	0.6–4.5 pF Variable Capacitor, Johanson Gigatrim #27271SL
C14	0.5 pF Chip Capacitor, ATC #100B0R5BT500XT
C15	15 pF Chip Capacitor, ATC #100B150JT500XT
C17	0.1 pF Chip Capacitor, ATC #100B0R1BT500XT
C18	22 μ F, 35 V Tantalum Surface Mount Chip Capacitor, Kemet #T491X226K035AT
R1	560 k Ω , 1/4 W Chip Resistor, 0.08" x 0.13", Vishay #CRCW12065600FKEA
R2, R5	12 Ω , 1/4 W Chip Resistors, 0.08" x 0.13", Vishay #CRCW120612R0FKEA
R3, R4	91 Ω , 1/4 W Chip Resistors, 0.08" x 0.13", Vishay #CRCW120691R0FKEA



Freescle has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescle Semiconductor signature/-logo. PCBs may have either Motorola or Freescle markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. 1930 - 2000 MHz Broadband Test Circuit Component Layout



Z1	0.122" x 0.08" Microstrip	Z8	0.414" x 0.330" Microstrip
Z2	0.650" x 0.08" Microstrip	Z9	0.392" x 0.08" Microstrip
Z3	0.160" x 0.08" Microstrip	Z10	0.070" x 0.08" Microstrip
Z4	0.030" x 0.08" Microstrip	Z11	1.110" x 0.08" Microstrip
Z5	0.045" x 0.08" Microstrip	PCB	0.030" Glass Teflon®, 2 oz Copper, 3" x 5" Dimensions, Arlon GX0300-55-22, $\epsilon_r = 2.55$
Z6	0.291" x 0.08" Microstrip		
Z7	0.483" x 0.330" Microstrip		

Figure 3. 1810 - 1880 MHz Broadband Test Circuit Schematic

Table 5. 1810 - 1880 MHz Broadband Test Circuit Component Designations and Values

Designators	Description
B1, B2, B3, B4, B5, B6	Surface Mount Ferrite Beads, 0.120" x 0.170" x 0.100", Fair Rite #2743029446
C1, C16	470 μ F, 63 V Electrolytic Capacitors, Multicomp #EKME630ELL471MK25S
C2, C9, C12, C17	0.6-4.5 pF Variable Capacitors, Johanson Gigatrim #27271SL
C3	0.8-8.0 pF Variable Capacitor, Johanson Gigatrim #27291SL
C4, C13	0.1 μ F Chip Capacitors, Kemet #CDR33BX104AKYS
C5, C14	100 pF Chip Capacitors, ATC #100B101JT500XT
C6, C8, C11, C15	12 pF Chip Capacitors, ATC #100B120JT500XT
C7, C10	1000 pF Chip Capacitors, ATC #100B102JT500XT
L1	3 Turns, 27 AWG, 0.087" OD, 0.050" ID, 0.053" Long, 6.0 nH
L2	5 Turns, 27 AWG, 0.087" OD, 0.050" ID, 0.091" Long, 15 nH
L3, L4	9 Turns, 26 AWG, 0.080" OD, 0.046" ID, 0.170" Long, 30.8 nH
L5	4 Turns, 27 AWG, 0.087" OD, 0.050" ID, 0.078" Long, 10 nH
R1, R2, R3, R4, R5, R6	12 Ω , 1/4 W Fixed Film Chip Resistors, Vishay #CRCW120612R0FKEA

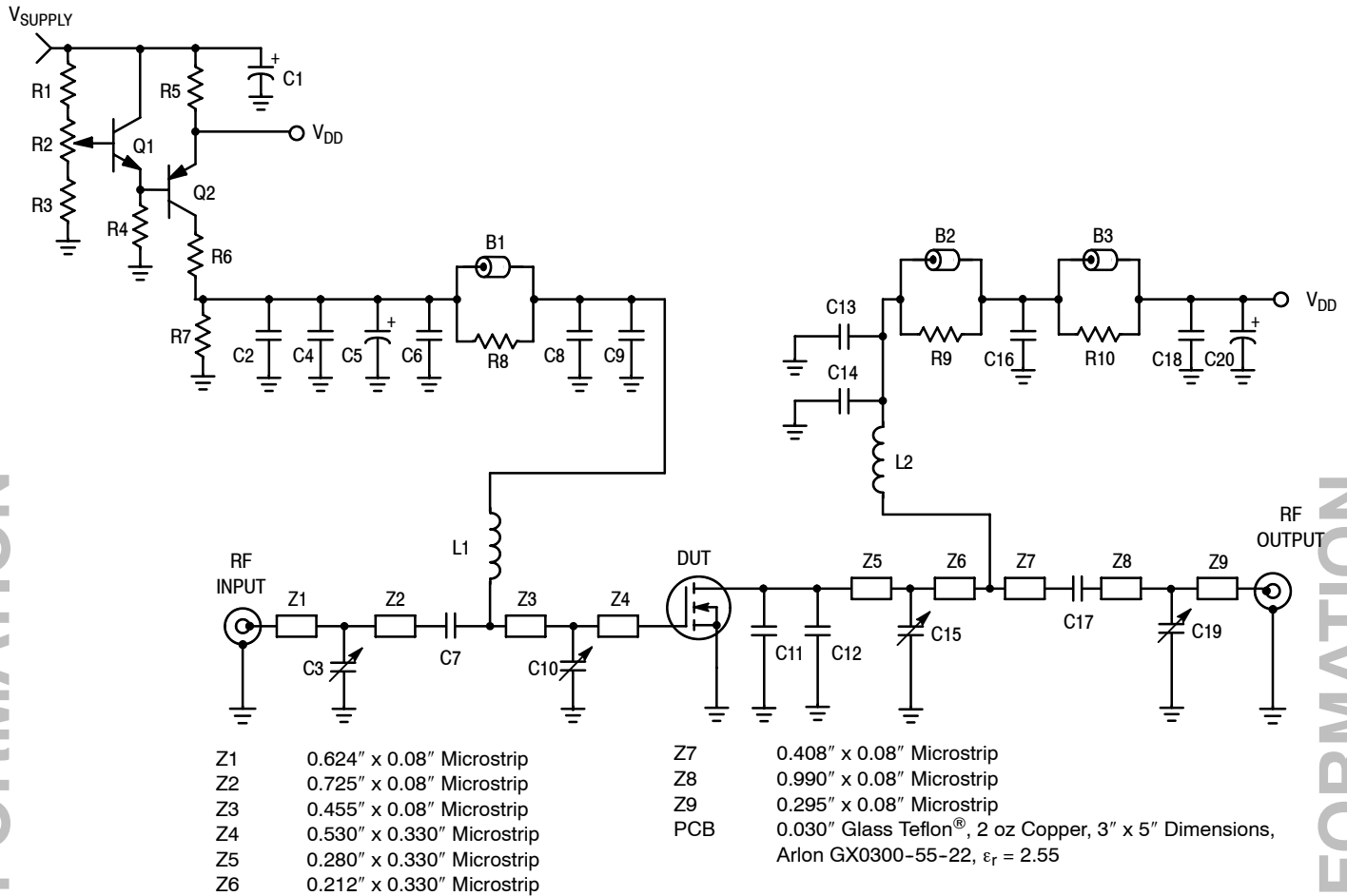
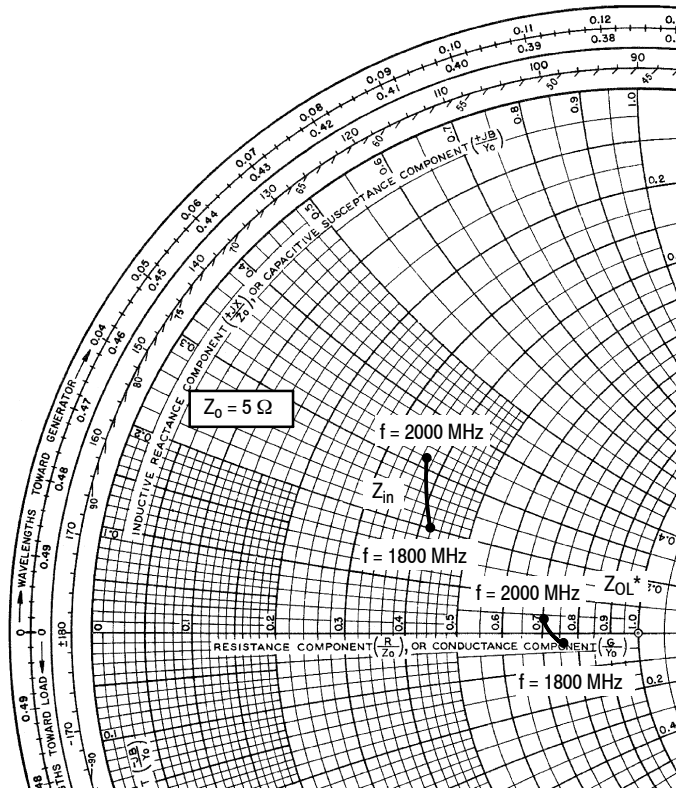


Figure 4. Class A Broadband Test Circuit Schematic

Table 6. Class A Broadband Test Circuit Component Designations and Values

Designators	Description
B1, B2, B3	Ferrite Beads, Ferroxcube #56-590-65-3B
C1, C20	470 μ F, 63 V Electrolytic Capacitors, Multicomp #EKME630ELL471MK25S
C2	0.01 μ F Chip Capacitor, ATC #100B103JT50XT
C3, C10, C15	0.6-4.5 pF Variable Capacitors, Johanson #27271SL
C4, C16	0.02 μ F Chip Capacitors, ATC #100B203JT50XT
C5	100 μ F, 50 V Electrolytic Capacitor, Multicomp #MCHT101M1HB-1017-RH
C6, C7, C9, C14, C17	12 pF Chip Capacitors, ATC #100B120JT500XT
C8, C13	51 pF Chip Capacitors, ATC #100B510JT500XT
C11, C12	0.3 pF Chip Capacitors, ATC #100B0R3CT500XT
C18	0.1 μ F Chip Capacitor, Kemet #CDR33BX104AKYS
C19	0.4-2.5 pF Variable Capacitor, Johanson #27285
L1	8 Turns, 0.042" ID, 24 AWG, Enamel
L2	9 Turns, 0.046" ID, 26 AWG, Enamel
Q1	NPN, 15 W, Bipolar Transistor, On Semi #MJD31T4G
Q2	PNP, 15 W, Bipolar Transistor, On Semi #MJD32T4G
R1	RC 1/4 200 10% A, Stack Pole
R2	1.0 k Ω , 1/2 W Potentiometer, Bourns, 3224W
R3	RC 1/4 13 K 5% A, Stack Pole
R4, R6, R7	390 Ω , 1/4 W Chip Resistors, Vishay #CRCW12063900FKEA
R5	1.0 Ω , 10 W 1% Resistor, Dale #RE65G1R00C02
R8, R9, R10	12 Ω , 1/8 W Chip Resistors, Vishay #CRCW120612R0FKEA



$V_{DD} = 26\text{ V}$, $I_{DQ} = 75\text{ mA}$, $P_{out} = 10\text{ W (PEP)}$

f MHz	Z_{in} Ω	Z_{OL}^* Ω
1800	$2.1 + j1.0$	$3.8 - j0.15$
1860	$2.05 + j1.15$	$3.77 - j0.13$
1900	$2.0 + j1.2$	$3.75 - j0.1$
1960	$1.9 + j1.4$	$3.65 + j0.1$
2000	$1.85 + j1.6$	$3.55 + j0.2$

Z_{in} = Complex conjugate of source impedance.

Z_{OL}^* = Complex conjugate of the optimum load impedance at given output power, voltage, IMD, bias current and frequency.

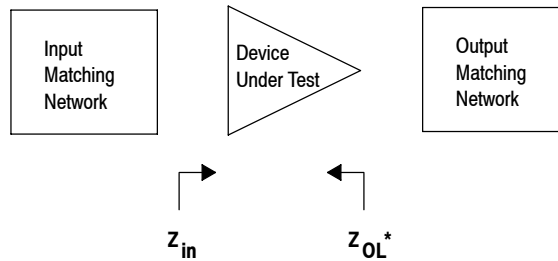
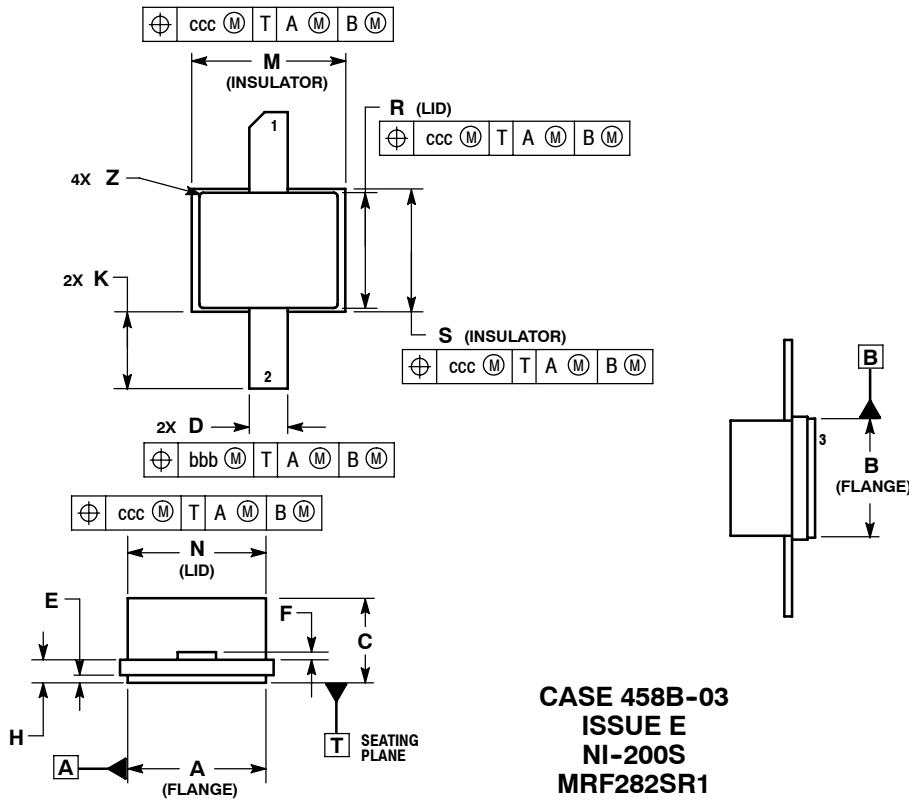


Figure 5. Series Equivalent Input and Output Impedance

PACKAGE DIMENSIONS



- NOTES:
1. CONTROLLING DIMENSIONS: INCHES.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. ALL DIMENSIONS ARE SYMMETRICAL ABOUT CENTERLINE UNLESS OTHERWISE NOTED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.180	0.190	4.572	4.83
B	0.140	0.150	3.556	3.81
C	0.082	0.116	2.083	2.946
D	0.047	0.053	1.194	1.346
E	0.004	0.010	0.102	0.254
F	0.004	0.006	0.102	0.152
H	0.025	0.031	0.635	0.787
K	0.060	0.110	1.524	2.794
M	0.197	0.203	5.004	5.156
N	0.177	0.183	4.496	4.648
R	0.147	0.153	3.734	3.886
S	0.157	0.163	3.988	4.14
Z	---	0.020	---	0.508
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
 PIN 1. DRAIN
 PIN 2. GATE
 PIN 3. SOURCE

CASE 458B-03
ISSUE E
NI-200S
MRF282SR1

ARCHIVE INFORMATION

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REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
16	Oct. 2008	<ul style="list-style-type: none"> • MRF282-1 Rev. 16 (MRF282SR1) data sheet archived. Part no longer manufactured. See MRF282-2 Rev. 17 for MRF282ZR1. Data sheet split due to change in part life cycle.

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